

1. Scope :

This specification applies to NPN silicon phototransistor chips,
Device No. ST-2016A.

2. Structure :

2-1. Planar type.

2-2. Electrodes :

N (Collector) side : Gold alloy.

P (Base) side : Aluminum alloy.

N (Emitter) side : Aluminum alloy.

3. Size :

3-1. Chip size : 15.7 mils x 15.7 mils (0.400 mm x 0.400 mm).

3-2. Chip thickness : 7.5 ± 1.5 mils (0.191 ± 0.038 mm).

3-3. Active area : 11.0 mils x 11.0 mils (0.280 mm x 0.280 mm).

3-4. Pattern drawing : refer to the attached drawing.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Collector-emitter Breakdown Voltage	BVCEO	IC=100uA IB=0	80			V
Emitter-collector Breakdown Voltage	BVECO	IE=10uA IB=0	7			V
Collector dark current	ICEO	VCE=20V H=0mw/cm ²			60	nA
Collector-emitter Saturation Voltage	VCE(S)	Ic=2mA IB=100uA			0.2	V
Current gain	hFE	VCE=5V IC=2mA	200			

